

FDFMA2P853

Integrated P-Channel PowerTrench[®] MOSFET and Schottky Diode

General Description

This device is designed specifically as a single package solution for the battery charge switch in cellular handset and other ultra-portable applications. It features a MOSFET with low on-state resistance and an independently connected low forward voltage schottky diode for minimum conduction losses.

The MicroFET 2x2 package offers exceptional thermal performance for it's physisize and is well suited to linear mode applications.

Features

MOSFET:

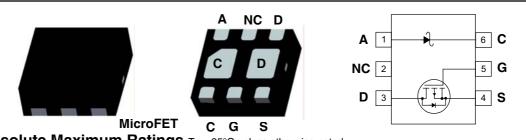
■ -3.0 A, -20V. $R_{DS(ON)} = 120 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 160 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$

 $R_{DS(ON)} = 240 \text{ m}\Omega @ V_{GS} = -1.8 \text{ V}$

Schottky:

V_F < 0.46 V @ 500 mA

- Low Profile 0.8 mm maximun in the new package MicroFET 2x2 mm
- RoHS Compliant



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

| Symbol | Parameter | | Ratings | Units | |
|-----------------------------------|--|-----------|-------------|-------|--|
| V _{DSS} | MOSFET Drain-Source Voltage | | -20 | V | |
| V _{GSS} | MOSFET Gate-Source Voltage | | ±8 | V | |
| I _D | Drain Current -Continuous | (Note 1a) | -3.0 | | |
| | -Pulsed | | -6 | — A | |
| V _{RRM} | Schottky Repetitive Peak Reverse voltage | | 30 | V | |
| I _O | Schottky Average Forward Current | (Note 1a) | 1 | A | |
| P _D | Power dissipation for Single Operation | (Note 1a) | 1.4 | w | |
| | Power dissipation for Single Operation | (Note 1b) | 0.7 | vv | |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | | -55 to +150 | °C | |

Thermal Characteristics

| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 86 | |
|-----------------|---|-----------|-----|------|
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient | (Note 1b) | 173 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1c) | 86 | °C/W |
| R_{\thetaJA} | Thermal Resistance, Junction-to-Ambient | (Note 1d) | 140 | |

Package Marking and Ordering Information

| | | | Quantity |
|--------------|-----------|-----|------------|
| .853 FDFMA2P | 853 7inch | 8mm | 3000 units |

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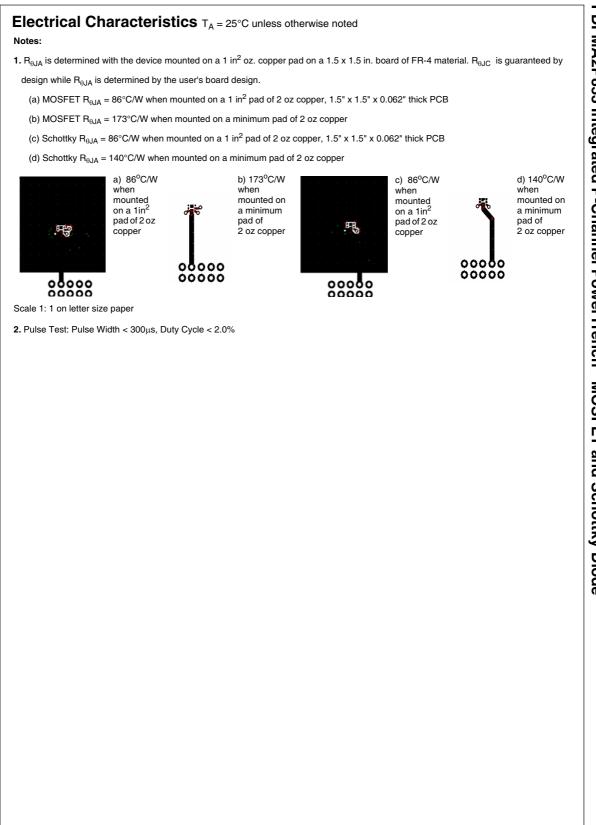
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| Symbol | Parameter | Test Conditions | | Min | Тур | Max | Units |
|--|---|---|---|------|------------|------------|-------|
| Off Char | acteristics | | | | | | |
| BV _{DSS} | Drain–Source Breakdown Voltage | V _{GS} = 0 V, | I _D = -250 μA | -20 | | | V |
| | Breakdown Voltage Temperature | 1 | Referenced to 25°C | | -12 | | mV/°C |
| ΔΤ _J | Coefficient | | | | | <u> </u> | |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = -16 V$, | | | | -1 | μA |
| GSS | Gate-Body Leakage | $V_{GS} = \pm 8 V$, | $V_{DS} = 0 V$ | | | ±100 | nA |
| On Chara | acteristics (Note 2) | - | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}$, | | -0.4 | -0.7 | -1.3 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | I_D = –250 µA, Referenced to 25°C | | | 2 | | mV/°C |
| R _{DS(on)} | Static Drain–Source | $V_{GS} = -4.5 V,$ | | | 90 | 120 | mΩ |
| | On–Resistance | $V_{GS} = -2.5 V,$ $V_{GS} = -1.8 V.$ | | | 120 172 | 160 240 | |
| | | 33 , | $T_D = -1.0 \text{ A}$ $T_D = -3.0 \text{ A}, T_J = 125^{\circ}\text{C}$ | | 118 | 160 | |
| I _{D(on)} | On–State Drain Current | $V_{GS} = -4.5 V,$ | | -20 | | | A |
| g _{FS} | Forward Transconductance | $V_{DS} = -5 V,$ | | 20 | 7 | | s |
| | | · · · · · · · · · · · · · · · · · · · | | 1 | | I | |
| | Characteristics | | | | 425 | | |
| Ciss | Input Capacitance | $V_{DS} = -10 V$, | $V_{GS} = 0 V,$ | | 435 | | pF |
| Coss | Output Capacitance | f = 1.0 MHz | | | 80 | | pF |
| Crss | Reverse Transfer Capacitance | | | L | 45 | | pF |
| | g Characteristics (Note 2) | 1 | | | | | |
| t _{d(on)} | Turn–On Delay Time | $V_{DD} = -10 V$, $I_D = -1 A$, $V_{GS} = -4.5 V$, $R_{GEN} = 6 \Omega$ | | | 9 | 18 | ns |
| t _r | Turn–On Rise Time | $v_{GS} = -4.5 V,$ | $\pi_{\text{GEN}} = 0 \Omega$ | | 11 | 19 | ns |
| t _{d(off)} | Turn–Off Delay Time | 4 | | | 15 | 27 | ns |
| t _f | Turn–Off Fall Time | | | | 6 | 12 | ns |
| Qg | Total Gate Charge | V _{DS} = -10 V, V _{GS} = -4.5 V | $I_{\rm D} = -3.0 {\rm A},$ | | 4 | 6 | nC |
| Q _{gs} | Gate–Source Charge | v _{GS} – –4.5 v | | | 0.8 | | nC |
| Q _{gd} | Gate–Drain Charge | | | | 0.9 | | nC |
| Drain-Sc | ource Diode Characteristics | and Maximu | m Ratings | | | | |
| ls | Maximum Continuous Drain-Sourc | ¥ | | | | -1.1 | A |
| V _{SD} | Drain–Source Diode Forward Voltage | V _{GS} = 0 V, | I _S = -1.1 A (Note 2) | | -0.8 | -1.2 | V |
| t _{rr} | Diode Reverse Recovery Time | I _F = −3.0 A, dI _F /dt = 100 A/μs | | | 17 | | ns |
| Q _{rr} | Diode Reverse Recovery Charge | | | | 6 | | nC |
| <u>Schottky</u> | Diode Characteristics | | | | | | |
| I _R | Reverse Leakage | V _R = 5 V | T _J = 25°C | | 9.9 | 50 | μA |
| | | | T _J = 125°C | | 2.3 | 10 | mA |
| I _R | Reverse Leakage | V _R = 20 V | T _J = 25°C | | 9.9 | 100 | μA |
| | | | T _J = 85°C | | 0.3 | 1 | mA |
| | - | | T _J = 125°C | | 2.3 | 10 | mA |
| V _F | Forward Voltage | I _F = 500mA | T _J = 25°C | | 0.4 | 0.46 | V |
| | | | T _J = 125°C | | 0.3 | 0.35 | |
| VF | Forward Voltage | I _F = 1A | T _J = 25°C | | 0.5 | 0.55 | V |
| | 1 | | T _J = 125°C | 1 | 0.49 | 0.54 | |

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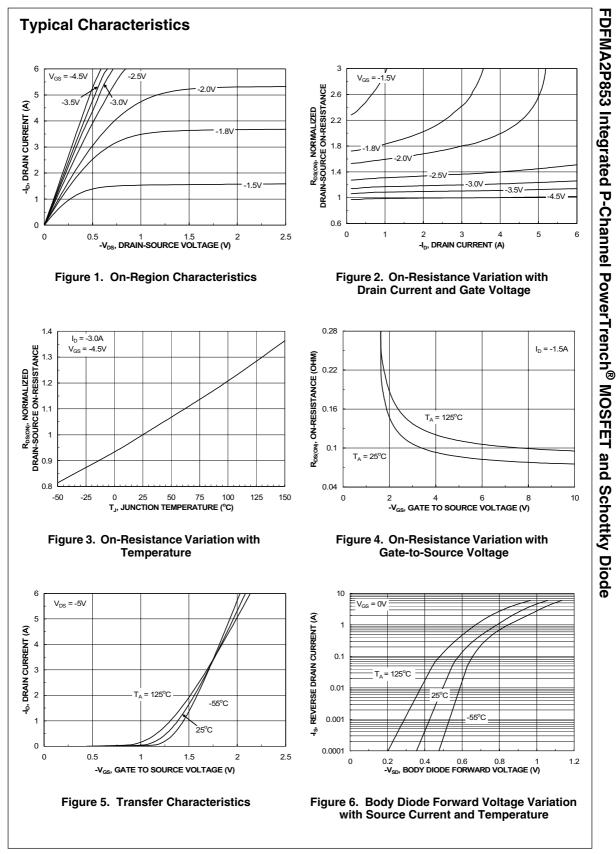
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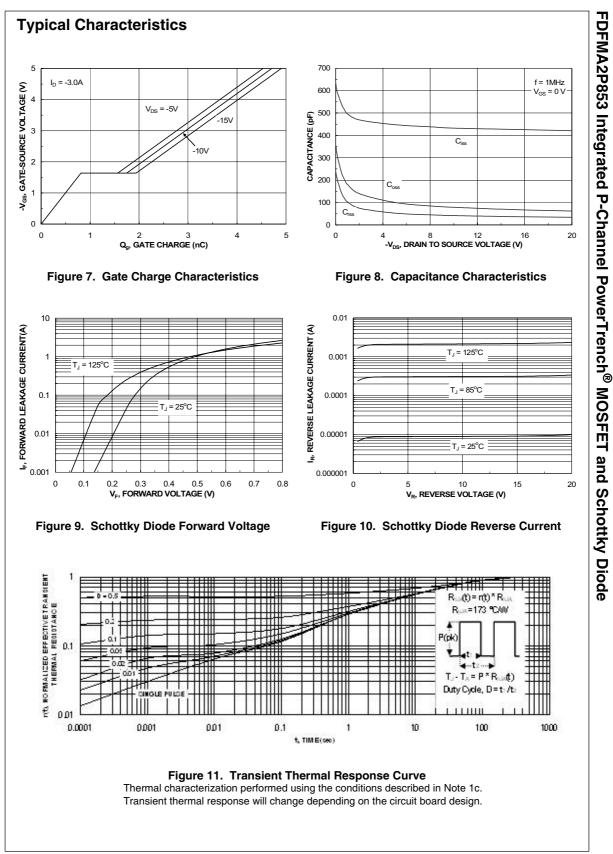


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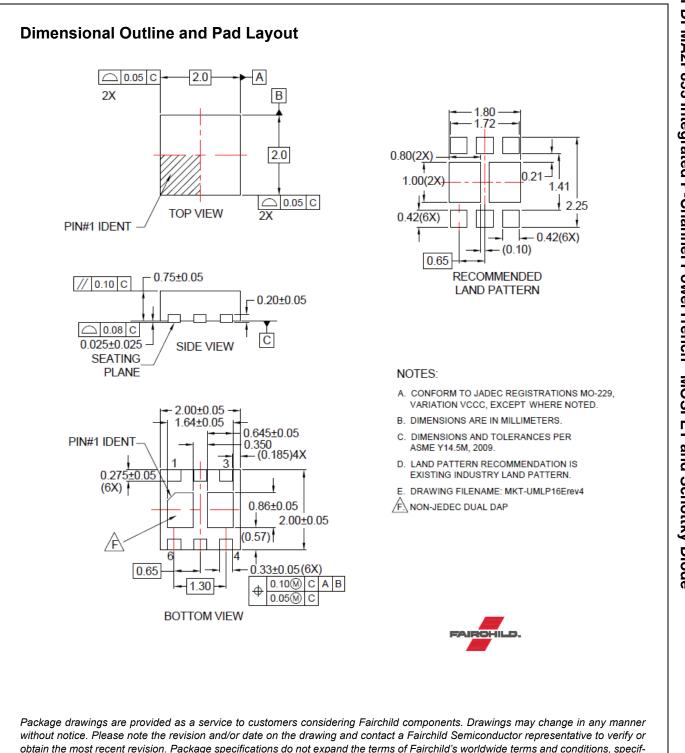
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